

Technical Meeting

Hydrogen Supersaturation and Defect Stabilization

Thermodynamics Models based on DFT data for Hydrogen Supersaturation and Defects Stabilization

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11-12 April 2022 Aix-en-Provence, France









H Supersaturation & V Stabilization, 11-12 April 2022

- Density Functional Theory
 - Statistic Thermodynamics (Gibbs free energy)

2. Thermodynamic models for vacancies

- 3. Supersaturation and vacancy stabilization
- 4. Discussion

Density Functional Theory – *electronic energy*

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Calculating the electronic energy of a system of electrons and nuclei

- Should be done using Quantum Mechanics
- Achieved through solving the Schrödinger equation
- Solutions not known, approximation, Hartree-Fock
- Limitation: the wave-function depends on too many variables $\Psi(r_1, r_2, ..., r_N)$ for a system of N electrons



An alternative: the Density Functional Theory

- The electronic density $\rho(r)$ only depends on three space variables
- The idea is to compute $E[\rho]$
- The question is how ?



Density Functional Theory – *total energy*

$$E^{elec}[\rho] = E_{kin}[\rho] + E_{electron-nuclei}[\rho] + E_{electron-electron}[\rho] + E_{electron-electron}[\rho] + E_{electron-electron}[\rho]$$
Quantum terms :
$$E_{kin}[\rho] - Known for non-interacting electrons$$

$$E_{electron-electron}[\rho] - approximation$$
eXchange-Correlation functional
$$E_{electron-electron}[\rho] + E_{nuclei-nuclei}$$
Ground state energy
Does not include the Temperature

Density Functional Theory



At T = 0K, only v=0 is populated.

- vibrational frequencies

Then, energy levels v populated with increasing temperature.

Bulk system of N atoms

3N - 3 frequencies v_i (phonons)

Energy levels are populated with increasing temperature

Vibrational energy depending on the temperature

Distance

The energy of the system is made temperature dependent

 $E_{tot}(T) = E^{DFT}(0K) + E_{vib}(T)$



- Density Functional Theory
- Statistic Thermodynamics

2. Thermodynamic models for vacancies creation

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Statistic Thermodynamics – State function Energy



Statistic Thermodynamics – *Toward equilibria*

Criterion for stability ?



Statistic Thermodynamics

– State function Entropy



$$S^{vib}(T, \mathbf{v}_j) = k_B \sum_{j=1}^{n_{vib}} \left[\frac{h\mathbf{v}_j}{k_B T} \frac{1}{\exp\left(\frac{h\mathbf{v}_j}{k_B T}\right) - 1} - \ln\left(1 - \exp\left(-\frac{h\mathbf{v}_j}{k_B T}\right)\right) \right]$$

Configurational entropyCreating vacanciesN lattice sitesN lattice sites N_{at} atoms at lattice sites n_V vacancies at lattice sites $N = N_{at} + n_V$ Number of configuration $\Omega = \frac{(N_{at} + n_v)!}{N_{at}! n_V!}$

Entropy (Boltzmann definition)

 $S(T) = k_B \ln \Omega$

Statistic Thermodynamics – Equilibrium conditions





2. Thermodynamic models for vacancies



- Results of the model
- Chemical potential and flux
- 3. Supersaturation and vacancy stabilization
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Electronic structure DFT calculations

Molecule H ₂	Interstitial H _i	Vacancy V	VH_j with j = 0 - 12
$e_{H_2}^{DFT}$	$e \frac{DFT}{H_i}$	e _V ^{DFT}	$e_{VH_j}^{DFT}$
v_{H_2}	$\sum_{k=1}^{3} \nu_k$	orational frequencies DFT calculations	$\sum_{k=1}^{3j} \nu_k$



$$g_j = e_j - T \cdot s_j \qquad G(T, p, n_{H_2}, n_{H_i}, n_V, n_{VH_1} \dots, n_{VH_{12}}) = \sum_j n_j \cdot g_j(T) - T \cdot S^{conf}(T)$$

H₂ Gas ideal gas

$$g_{H_2} = g_{H_2}^{\circ} + k_B T \ln \frac{P}{P^{\circ}}$$

$$g_{H_2}^{\circ} = \left(e_{H_2}^{DFT} + e_{H_2}^{vib} + e_{H_2}^{rot} + e_{H_2}^{trans} + PV\right) - T\left(s_{H_2}^{vib} + s_{H_2}^{rot} + s_{H_2}^{\circ trans}\right)$$

High pressure : Tkacz and Litwiniuk, J. Alloys Compounds 330-332 (2002) 89-92

The minimizing against

 $n_{H_2}, n_{H_i}, n_V, n_{VH_1} \dots, n_{VH_{12}}$

Composition of the system at equilibrium



High pressure : Tkacz and Litwiniuk, J. Alloys Compounds 330-332 (2002) 89-92



2. Thermodynamic models for vacancies

• The model



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Formation of vacancies induced by interstitial H atoms

N. Fernandez, Y. Ferro, D. Kato, Acat Mater 94 (2015) 307-318



Fig. 8. Fractions x_j of vacancy type VH_j in tungsten at thermodynamic equilibrium for a total fraction of hydrogen $x_H = 10^{-5}$.



$$\boldsymbol{x_{H_i}}(\boldsymbol{T}) \approx \gamma \exp\left[-\frac{\boldsymbol{g_{H_i}} - \boldsymbol{\mu}}{k_B T}\right]$$
$$\boldsymbol{x_{VH_j}}(\boldsymbol{T}) \approx \omega_j \exp\left[-\frac{\boldsymbol{g_{VH_j}} - j \boldsymbol{\mu}}{k_B T}\right]$$

Interstitial H atoms impose a high chemical potential This induces a high fraction of VHj vacancies High temperature entropy favors interstitials

→ Vacancies are depopulated

Driving forces for the formation of Super Abundant Vacancies

Sites	Energies (eV)	
eint	0.93	
e_0	3.25	
e_1	2.99	
e_2	2.73	
e3	2.57	
e 4	2.54	
<i>e</i> 5	2.57	
e_6	2.83	
е7	3.48	
e_8	4.08	
eg	4.81	
e 10	5.60	
<i>e</i> 11	6.58	
e12	7.20	

SAV in Pd under High pressure

Y. Fukai and N. Okuma, PRL 73 (1994) 1640





 H_2

E. A Hodille et al. PRMat 2 (2018) 093802

Formation energy of VH_j is lower than empty V up to j=6

Pioneering works on Mg and AI - Ismer et al. PRB 80 (2009) 184110



Ismer et al. PRB 80 (2009) 184110

Chemical potential from Sugimoto & Fukai, Acta. Metal. Mater 40 (1992) 2327

VHj formation in W



Chemical potential from Sugimoto et Fukai, Acta. Metal. Mater 40 (1992) 2327



2. Thermodynamic models for vacancies

- The model
- Results of the model
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Chemical potential fixed by the flux in the sub-surface

E. A Hodille, N. Fernandez, Z. A. Piazza, M. Ajmalghan, Y. Ferro et al. PRMat 2 (2018) 093802



Chemical potential fixed by the flux in the sub-surface

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Incident flux $\phi_{inc} = 10^{19} m^{-2} s^{-1}$ Incident ion energy E_{inc} = 500 eV/ion. The flux fixes $\mathbf{H}_{\text{int}}\dots$

- H_{int} fixes the chemical potential...
- ... and the fraction of VH_j vacancies

$$\boldsymbol{x}_{H_i} = \boldsymbol{R}_p \cdot (1 - r) \cdot \frac{\phi_{ion}}{\rho_W} \cdot \frac{1}{D(T)}$$

$$\begin{aligned} \mathbf{x}_{H_i} \left(\mathbf{T} \right) &\approx \gamma \exp \left[- \frac{\mathbf{g}_{H_i} - \boldsymbol{\mu}}{k_B T} \right] \\ \mathbf{x}_{VH_j} \left(\mathbf{T} \right) &\approx \omega_j \exp \left[- \frac{\mathbf{g}_{VH_j} - j \,\boldsymbol{\mu}}{k_B T} \right] \end{aligned}$$

Vacancy depopulation with increasing temperature

Chemical potential fixed by the flux in the sub-surface



The fraction of hydrogen interstitial sites is plotted in dotted lines

3-Super-Abundant Vacancies



No Impact of E_i Nishijima et al. NF 61 (2021) 116028



Concours Poste 986-987 Pr 46-3

2. Thermodynamic models for vacancies

3. Supersaturation and vacancy stabilization

→ Super Saturated Layers

Vacancy Stabilization

4. Discussion

Super-Saturated Layers

SSL forms within 10 nm

215 eV/D+ or 415 eV/H+



L. Gao et al. NF 57 (2017) 016026

L. Gao et al. Acta. Matter 201 (2020) 55-62

Mechanisms for vacancy stabilization ?



Hydrogen stabilizes vacancies

E. A Hodille et al. PRMat 2 (2018) 093802

Super-Saturated Layers

SSL forms within 10 nm

215 eV/D+ or 415 eV/H+



5eV/W at., well below 9eV/W at. (displ. Thr.)

L. Gao et al. NF 57 (2017) 016026

L. Gao et al. Acta. Matter 201 (2020) 55-62

Mechanisms for vacancy stabilization ?



 $E_f (VH_6+SIA) = 12.1 \text{ eV}$ 0.6 eV smaller than $E_f (VH_6) + E_f (SIA)$

Kato et al. NF 55 (2015) 083019

Crowdion-SIA (and others) stabilizes vacancies Prevent them from recombining

Hydrogen stabilizes vacancies

Super-Saturated Layers

SSL forms within 10 nm

215 eV/D+ or 415 eV/H+



5eV/W at., well below 9eV/W at. (displ. Thr.)

L. Gao et al. NF 57 (2017) 016026

L. Gao et al. Acta. Matter 201 (2020) 55-62

Mechanisms for vacancy stabilization ?



Binding energy of vacancies increases when vacancies grow

Crowdion-SIA (and others) stabilizes vacancies Hydrogen stabilizes vacancies

Super-Saturated Layers

SSL forms within 10 nm

215 eV/D+ or 415 eV/H+ 5eV/W at., well below 9eV/W at. (displ. Thr.) 1.0x10²² 0,15 300 Y: y yield of HSSL Sigmoid fit of Y 8,0x10²¹ 250 ^{0,12} (D content in DSSL concentration (at. 200 6,0x10 0,09 Y (cts/μC) 150 4,0x10²¹ 0,06 100 0,03 2,0x10²¹ 50 0,00 J 0.0 0 0 3 6 12 15 18 Depth in W (nm)

L. Gao et al. NF 57 (2017) 016026

L. Gao et al. Acta. Matter 201 (2020) 55-62

Mechanisms for vacancy stabilization ?



More energy is required to dissociate the Frenkel pair in the absence of Hydrogen

Dynamic of the process ?

2. Thermodynamic models for vacancies

3. Supersaturation and vacancy stabilization

Super Saturated Layers



Vacancy Stabilization

4. Discussion

SAV formation in damaged W – Defect Stabilization

M. Markelj et al., 59 (2019) 086050



SAV formation in damaged W – Defect Stabilization

M. Markelj et al., 59 (2019) 086050



No help from the Thermo. Model

- SSL are formed in the near surface
- Vacancies annihilate with increasing T
 → higher mobility of the atom
- Decoration reveals the V remaining after damaging

SAV formation in damaged W – Defect Stabilization

M. Markelj et al., 59 (2019) 086050





SAV formation in damaged W – Defect Stabilization



With temperature, mechanism for V stab less and less efficient

SAV formation in damaged W – Defect Stabilization

M. Simmonds et al., 59 (2019) 086050



Complies with the Thermo model

To be discussed ...

2. Thermodynamic models for vacancies

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4. Discussion

- Mechanisms for SSL formation and V stab are probably the same
- H in V would stabilize a V and prevent it to recombines with SIA
- Thermal V are created at the surface. W atoms bring enough energy to create additional vacancies that would be stabilized with H. No need for collision cascade and Frankel pairs.
- The stress around VHj should be at shorter distance than around V. In addition, VHj is much less mobile the V. The cross section for VHj+SIA recombination is smaller than V + SIA.
- SSL are formed in other metals like Mo, Fe, steel, not Cu that display higher Ef for V creation
- Hy SSL are formed at T=800K. Is it because of the flux that bring μ so high ?

Thanks for your attention ...

... and sorry for being that long.







